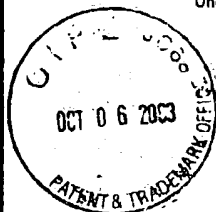


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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	1
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**Complete if Known**

Application Number	10/085.759	
Filing Date	28 February 2002	
First Named Inventor	Michel Luc Cote	
Group Art Unit	1752	
Examiner Name	<del>Unassigned</del> ROSASCO	
Attorney Docket Number	NMTI 1002-6	

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## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

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**Examiner  
Signature**

A. Zucco

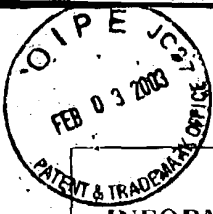
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<sup>1</sup> Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

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SHEET 1 of 3

INFORMATION DISCLOSURE  
CITATION

PTO-1449

Atty. Docket No.

NMTI 1002-6

Serial No.

10/085.759

Applicant

CÔTÉ, Michel Luc

Filing Date

2/28/2002

Group

1756

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## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
EC	6,420,074 B2	7/16/2002	Wang et al.	430	5	12/7/2000
	6,436,590 B2	8/20/2002	Wang, et al.	430	5	4/20/2001
	2002/0083410 A1	6/27/2002	Wu, et al.	716	19	12/5/2001
	2002/0122994 A1	9/5/2002	Cote, et al.	430	5	2/28/2002
	2002/0127479 A1	9/12/2002	Pierrat	430	5	2/6/2002
	2002/0129327 A1	9/12/2002	Pierrat, et al.	716	19	11/15/2001
	2002/0136964 A1	9/26/2002	Pierrat	430	5	3/23/2001
	2002/0142231 A1	10/3/2002	Kling, et al.	430	5	4/25/2001
	2002/0142232 A1	10/3/2002	Kling, et al.	430	5	4/25/2001
	2002/0144232 A1	10/3/2002	Ma, et al.	716	21	5/31/2001
	2002/0152454 A1	10/17/2002	Cote, et al.	716	21	6/7/2002
EC	2002/0155363 A1	10/24/2002	Cote, et al.	430	5	6/7/2002

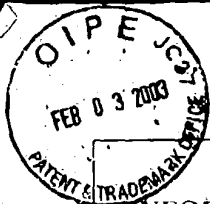
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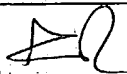

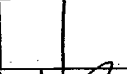

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		<b>Applicant</b> CÔTÉ, Michel Luc		<b>RECEIVED</b> FEB 5 2003 TC 1700			
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				<b>Group</b> 1756			
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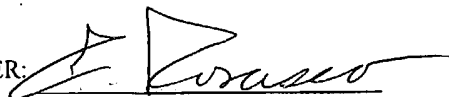
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		<b>Applicant</b> CÔTÉ, Michel Luc	<b>Group</b> 1756
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<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
EXAMINER'S INITIALS	CITATION		
	Cooke, M., "OPC/PSM Designs For Poly Gate Layers", European Semiconductor, Vol. 22, No. 7, pp. 57-59, July 2000.		
	Granik, Y., et al., "Sub-Resolution Process Windows And Yield Estimation Technique Based On Detailed Full-Chip CD Simulation", SPIE, Vol. 4182, pp. 335-341 (2000).		
	Plat, M., et al., "The Impact of Optical Enhancement Techniques on the Mask Error Enhancement Function (MEEF)", SPIE, Vol. 4000, pp. 206-214, March 1-3, 2000.		
	Mansuripur, M., et al., "Projection Photolithography", Optics & Photonics News 11, 17 pages, February 2000.		

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		<b>Applicant</b> CÔTÉ, Michel Luc		<b>Group</b> 1752		
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	5,308,741	5/3/1994	Kemp	430	312	7/31/1992
	5,324,600	6/28/1994	Jinbo, et al.	430	5	7/7/1992
	5,364,716	11/15/1994	Nakagawa, et al.	430	5	9/3/1992
	5,472,814	12/5/1995	Lin	430	5	11/17/1994
	5,523,186	6/4/1996	Lin, et al.	430	5	12/16/1994
	5,527,645	6/18/1996	Pati, et al.	430	5	11/17/1994
	5,537,648	7/16/1996	Liebmann, et al.	395	500	8/15/1994
	5,538,815	7/23/1996	Oi, et al.	430	5	9/14/1993
	5,565,286	10/15/1996	Lin	430	5	11/17/1994
	5,573,890	11/12/1996	Spence	430	311	7/18/1994
	5,595,843	1/21/1997	Dao	430	5	3/30/1995
	5,620,816	4/15/1997	Dao	430	5	10/13/1995
	5,635,316	6/3/1997	Dao	430	5	10/13/1995
	5,636,131	6/3/1997	Liebmann, et al.	364	490	5/12/1995
	5,702,848	12/30/1997	Spence	430	5	8/23/1996
	5,761,075	6/2/1998	Oi, et al.	364	488	5/31/1996
	5,766,804	6/16/1998	Spence	430	5	8/23/1996
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	5,807,649	9/15/1998	Liebmann, et al.	430	5	10/31/1996
	5,858,580	1/12/1999	Wang, et al.	430	5	9/17/1997
	5,923,562	7/13/1999	Liebmann, et al.	364	488	10/18/1996
<i>DL</i>	5,923,566	6/13/1999	Galan, et al.	364	489	3/25/1997

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		CÔTÉ, Michel Luc				
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	5,998,068	12/7/1999	Matsuoka	430	5	1/27/1998
	6,057,063	5/2/2000	Liebmann, et al.	430	5	4/14/1997
	6,066,180	5/23/2000	Kim, et al.	716	19	3/15/1999
	6,083,275	7/4/2000	Heng, et al.	716	19	1/9/1998
	6,130,012	10/10/2000	May, et al.	430	5	1/13/1999
	6,139,994	10/31/2000	Broeke, et al.	430	5	6/25/1999
	6,185,727 B1	2/6/2001	Liebmann	716	19	12/12/1995
	6,228,539 B1	5/8/2001	Wang, et al.	430	5	1/12/1999
	6,251,549 B1	6/26/2001	Levenson	430	11	10/28/1999
	6,258,493 B1	7/10/2001	Wang, et al.	430	5	7/17/2000
	6,335,128 B1	1/1/2002	Cobb, et al.	430	5	9/28/1999
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<i>FL</i>	2001/0028985 A1	10/11/2001	Wang, et al.	430	5	4/20/2001

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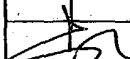
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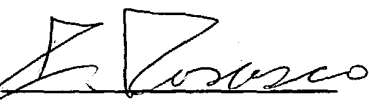
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		<b>Applicant</b> CÔTÉ, Michel Luc		<b>Group</b> 1752 <del>Not Yet Assigned</del>			
		<b>Filing Date</b> 2/28/2002					
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		<b>Applicant</b> CÔTÉ, Michel Luc	<b>Group</b> <u>1752</u> <del>Not Yet Assigned</del>
		<b>Filing Date</b> 2/28/2002	
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
<b>EXAMINER'S INITIALS</b>	<b>CITATION</b>		
<i>[Signature]</i>	Ackmann, P., et al., "Phase Shifting and Optical Proximity Corrections to Improve CD Control on Logic Devices in Manufacturing for Sub 0.35 um 1-Line", SPIE, Vol. 3051, pp. 146-153, March 12-14, 1997.		
	Matsuoka, K., et al., "Application of Alternating Phase-Shifting Mask to 0.16um CMOS Logic Gate Patterns", Matsushita Electric Ind. Co., Ltd. (9 pages).		
	Wang, R., et al., <del>Polarized</del> Phase Shift Mask: Concept, Design, and Potential Advantages to Photolithography Process and Physical Design", Motorola Semiconductor Product Sector (12 pages).		
	Ogawa, K., et al., "Phase Defect Inspection by Differential Interference", Lasertec Corporation (12 pages).		
	Pistor, T., "Rigorous 3D Simulation of Phase Defects in Alternating Phase-Shifting Masks", Panoramic Technology Inc. (13 pages).		
	Semmner, A., et al., "Application of 3D EMF Simulation for Development and Optimization of Alternating Phase Shifting Masks", Infineon Technologies AG (12 pages).		
	Wong, A., et al., "Polarization Effects in Mask Transmission", University of California Berkeley (8 pages).		
	Erdmann, A., "Topography Effects and Wave Aberrations in Advanced PSM-Technology", Fraunhofer Institute of Integrated Circuits (11 pages).		
	Granik, Y., et al., "CD Variation Analysis Technique and its Application to the Study of PSM Mask Misalignment", Mentor Graphics (9 pages).		
	Hanyu, et al., "New Phase-Shifting Mask with Highly Transparent SiO2 Phase Shifters", Fujitsu Laboratories Ltd. (11 pages).		
	Ishiwata, N., et al., "Fabrication of Phase-Shifting Mask", Fujitsu Limited (11 pages).		
	Levenson, M., et al., "Phase Phirst! An Improved Strong-PSM Paradigm", M.D. Levenson Consulting, Petersen Advanced Lithography, KLA-Tencor (10 pages).		
	Levenson, M., et al., "SCAA Mask Exposures and Phase Phirst Design for 110nm and Below", M.D. Levenson Consulting, Canon USA, Inc., JSR Microelectronics, Inc. (10 pages).		
<i>[Signature]</i>	Lin, B.J., "The Relative Importance of the Building Blocks for 193nm Optical Lithography", Linnovation, Inc. (12 pages).		

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		NMTI 1002-6	10/085,759
		Applicant	
		CÔTÉ, Michel Luc	
		Filing Date	Group
		2/28/2002	1752
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
	McCallum, M., et al., "Alternating PSM Mask Performance - a Study of Multiple Fabrication Technique Results", International SEMATECH (6 pages).		
	Morikawa, Y., et al., "100nm-alt.PSM Structure Discussion for ArF Lithography", Dai-Nippon Printing Co., Ltd. (15 pages).		
	Ozaki, T., et al., "A 0.15um KrF Lithography for 1Gb DRAM Product Using Highly Printable Patterns and Thin Resist Process", Toshiba Corporation (2 pages).		
	Rhyins, P., et al., "Characterization of Quartz Etched PSM Masks for KrF Lithography at the 100nm Node", Photonics, Inc., MIT Lincoln Lab, ARCH Chemicals, Finle Technologies, KLA-Tencor Corp. (10 pages).		
	Rosenbluth, A., et al., "Optimum Mask and Source Patterns to Print a Given Shape", IBM (17 pages).		
	Schmidt, R., et al., "Impact of Coma on CD Control for Multiphase PSM Designs", AMD, ASML (10 pages).		
	Sewell, H., et al., "An Evaluation of the Dual Exposure Technique", SVG Lithography Systems Inc. (11 pages).		
	Spence, C., et al., "Optimization of Phase-Shift Mask Designs Including Defocus Effects", AMD, Princeton University, Vecor Technologies Inc. (8 pages).		
	Suzuki, A., et al., "Multilevel Imaging System Realizing k1=-.3 Lithography", Canon Inc. (13 pages).		
	Vandenberghe, G., et al., "(Sub-)100nm Gate Patterning Using 248nm Alternating PSM", IMEC, Mentor Graphics (9 pages).		
	Fritze, M., et al., "100-nm Node Lithography with KrF?", MIT Lincoln Lab, Numerical Technologies, Photonics, Arch Chemicals (14 pages).		
	Fukuda, H., et al., "Patterning of Random Interconnect Using Double Exposure of Strong-Type PSMS", Hitachi Central Research Lab (8 pages).		
	Ferguson, R., et al., "Pattern-Dependent Correction of Mask Topography Effects for Alternating Phase-Shifting Masks", IBM Microelectronics, University of California Berkeley (12 pages).		
	Toubian, O., et al., "Phase and Transmission Errors Aware OPC Solution for PSM: Feasibility Demonstration", Mentor Graphics Corp. (7 pages).		

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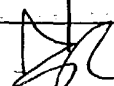
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	CÔTÉ, Michel Luc	
	<b>Filing Date</b>	<b>Group</b>
	2/28/2002	1752
		<del>Not Yet Assigned</del>

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

EXAMINER'S INITIALS	CITATION
762	Yanagishita, Y., et al., "Phase-Shifting Photolithography Applicable to Real IC Patterns", Fujitsu Limited (11 pages).
	Levenson, M., et al., "Improving Resolution in Photolithography with a Phase-Shifting Mask", IEEE, Transactions On Electron Devices, Vol. ED-29, No. 12, pp. 1828-1836, December 1982.
	Levenson, M., et al., "The Phase-Shifting Mask II: Imaging Simulations and Submicrometer Resist Exposures", IEEE Transactions on Electron Devices, Vol. ED-31, No. 6, pp. 753-763, June 1984.
	Terasawa, T., et al., "0.3-Micron Optical Lithography Using a Phase-Shifting Mask", SPIE, Optical/Laser Microlithography II, Vol. 1088, pp. 25-33, March 1989.
	Nitayama, A., et al., "New Phase Shifting Mask with Self-Aligned Phase Sifters for a Quarter Micron Photolithography", IEDM, pp. 3.3.1-3.3.4, December 3-6, 1989.
	Jinbo, H., et al., "0.2um or Less i-Line Lithography by Phase-Shifting-Mask Technology", IEEE, pp. 33.3.1-33.3.4 (1990).
	Neureuther, A., "Modeling Phase Shifting Masks", SPIE, 10th Annual Symposium On Microlithography, Vol. 1496, pp. 80-85 (1990).
	Yamanaka, T., et al., "A 5.9um <sup>2</sup> Super Low Power SRAM Cell Using a New Phase-Shift Lithography", IEDM, pp. 18.3.1-18.3.4 (1990).
	Inokuchi, K., et al., "Sub-Quarter Micron Gate Fabrication Process Using Phase-Shifting-Mask for Microwave GaAs Devices", Extended Abstracts Of The 1991 Intl. Conference On Solid State Devices And Materials, Yokohama, Japan, pp. 92-94 (1991).
	Inokuchi, K., et al., "Sub-Quarter-Micron Gate Fabrication Process Using Phase-Shifting Mask for Microwave GaAs Devices", Japanese Journal Of Applied Physics, Vol. 30, No. 12B, pp. 3818-3821, December 1991.
	Jinbo, H., et al., "Improvement of Phase-Shifter Edge Line Mask Method", Japanese Journal Of Applied Physics, Vol. 30, No. 11B, pp. 2998-3003, November 1991.
	Kimura, T., et al., "Subhalf-Micron Gate GaAs Mesfet Process Using Phase-Shifting-Mask Technology", IEEE, GaAs IC Symposium, pp. 281-284 (1991).
	Wiley, J., et al., "Phase Shift Mask Pattern Accuracy Requirements and Inspection Technology", SPIE, Integrated Circuit Metrology, Inspection, And Process Control V, Vol. 1464, pp. 346-355 (1991).
762	Hirai, Y., et al., "Automatic Pattern Generation System for Phase Shifting Mask", 1991 Symposium on VLSI Technology, Digest of Technical Papers, pp. 95-96, May 28-30, 1991.

EXAMINER: 762Date Considered: 2/4/04

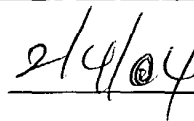
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		<b>Applicant</b> CÔTÉ, Michel Luc	<b>Group</b> 1752 <del>Not Yet Assigned</del>
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
<b>EXAMINER'S INITIALS</b>	<b>CITATION</b>		
	Wong, A., et al., "Investigating Phase-Shifting Mask Layout Issues Using a Cad Toolkit", IEEE, pp. 27.4.1-27.4.4 (1991).		
	Terasawa, T., et al., "Imaging Characteristics of Multi-Phase-Shifting and Half-tone Phase-Shifting Masks", Japanese Journal of Applied Physics, Vol. 30, No. 11B, pp. 2991-2997, November 1991.		
	Burggraaf, P., "Four More Significant Japanese Advances in Phase Shifting Technology", Semiconductor International, p. 16, December 1991.		
	Kemp, K., et al., "Optimized Phase Shift Mask Designs for Real Devices", KTI Microlithography Seminar, pp. 67-75, October 14-15, 1991.		
	Newmark, D., et al., "Phase-Shifting Mask Design Tool", SPIE - 11th Annual BACUS Symposium on Photmask Technology, Vol. 1604, pp. 226-235, September 25-27, 1991.		
	Nolscher, C., et al., "Investigation of Self-Aligned Phase-Shifting Reticles by Simulation Techniques", SPIE - Optical/Laser Microlithography IV, Vol. 1463, pp. 135-150 (1991).		
	Inoue, S., et al., "Simulation Study on Phase-Shifting Masks for Isolated Patterns", Japanese Journal of Applied Physics, Vol. 30, No. 11B, pp. 3010-3015, November 1991.		
	Watanabe, H., et al., "Detection and Printability of Shifter Defects in Phase-Shifting Masks", Japanese Journal of Applied Physics, Vol. 30, No. 11B, pp. 3016-3020, November 1991.		
	Watanabe, H., et al., "Pattern Transfer Characteristics of Transparent Phase Shifting Mask", Japanese Journal of Applied Physics, Vol. 30, No. 11B, pp. 3004-3009, November 1991.		
	Jinbo, H., et al., "Application of Blind Method to Phase-Shifting Lithography", IEEE, 1992 Symposium On VLSI Technology Digest Of Technical Papers, pp. 112-113 (1992).		
	Watanabe, H., et al., "Detection and Printability of Shifter Defects in Phase-Shifting Masks II Defocus Characteristics", Jpn. J. Appl. Phys., Vol. 31, pp. 4155-4160 (1992).		
	Pierrat, C., et al., "Phase-Shifting Mask Topography Effects on Lithographic Image Quality", IEEE, pp. 3.3.1-3.3.4 (1992).		
	Burggraaf, P., "Lithography's Leading Edge, Part 1: Phase-Shift Technology and Part 2: I-Line and Beyond", Semiconductor International, pp. 43-47 and 52-56, February 1992.		
	IBM, "Phase-Shift Mask Utilizing Silicon Oxy-Nitride as a Low Reflectivity Phase-Shift Layer", IBM Technical Disclosure Bulletin, Vol. 34, No. 10B, pp. 360-361, March 1992.		

EXAMINER:

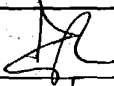



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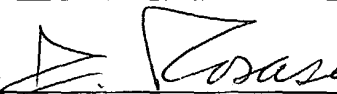


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<b>INFORMATION DISCLOSURE CITATION</b>  <b>PTO-1449</b>		Atty. Docket No.	Serial No.
		NMTI 1002-6	10/085,759
		Applicant	
		CÔTÉ, Michel Luc	
		Filing Date	Group
		2/28/2002	1752
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
	Brunner, T., et al., "170nm Gates Fabricated by Phase-Shift Mask and Top Anti-Reflector Process", SPIE, Optical/Laser Microlithography VI, Vol. 1927, pp. 182-189 (1993).		
	Lin, B.J., "Phase-Shifting Masks Gain an Edge", IEEE Circuits & Devices, pp. 28-35, March 1993.		
	Moriwa, A., et al., "Algorithm for Phase-Shift Mask Design with Priority on Shifter Placement", Jpn. J. Appl. Phys., Vol. 32, Pt. 1, No. 12B, pp. 5874-5879, December 1993.		
	Ooi, K., et al., "Computer Aided Design Software for Designing Phase-Shifting Masks", Jpn. J. Appl. Phys., Vol. 32, Pt. 1, No. 12B, pp. 5887-5891, December 1993.		
	Ohtsuka, H., et al., "Evaluation of Repair Phase and Size Tolerance for a Phase-Shift Mask", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2665-2668, November/December 1993.		
	Ronse, K., et al., "Comparison of Various Phase Shift Strategies and Application to 0.35um ASIC Designs", SPIE - Optical/Laser Microlithography VI, Vol. 1927, pp. 2-16 (1993).		
	Galan, G., et al., "Application of Alternating-Type Phase Shift Mask to Polysilicon Level for Random Logic Circuits", Jpn. J. Appl. Phys., Vol. 33, pp. 6779-6784 (1994).		
	Mizuno, F., et al., "Practical Phase-Shifting Mask Technology for 0.3um Large Scale Integrations", J. Vac. Sci. Technol. B, Vol. 12, No. 6, pp. 3799-3803, November/December 1994.		
	Pati, Y.C., et al., "Phase-Shifting Masks for Microlithography: Automated Design and Mask Requirements", J. Opt. Soc. Am., Vol. 11, No. 9, pp. 2438-2452, September 1994.		
	Stirniman, J., et al., "Wafer Proximity Correction and Its Impact on Mask-Making", Bacus News, Vol. 10, Issue 1, pp. 1, 3-7, 10-12, January 1994.		
	Waas, T., et al., "Automatic Generation of Phase Shift Mask Layouts", Microelectronic Engineering, Vol. 23, pp. 139-142 (1994).		
	Barouch, E., et al., "OPTIMASK: An OPC Algorithm for Chrome and Phase-Shift Mask Design", SPIE, Vol. 2440, pp. 192-206, February 1995.		
	Moriwa, A., et al., "Heuristic Method for Phase-Conflict Minimization in Automatic Phase-Shift Mask Design", Jpn. J. Appl. Phys., Vol. 34, Pt. 1, No. 12B, pp. 6584-6589, December 1995.		
	Langston, J., et al., "Extending Optical Lithography to 0.25um and Below", Solid State Technology, pp. 57-64, March 1995.		

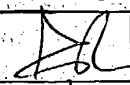
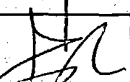
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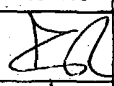
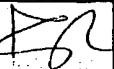
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<b>EXAMINER'S INITIALS</b>	<b>CITATION</b>		
	Nagahiro, Y., "Improved Mask Technique for Photolithography Applied to 0.25um LSI - Improvement of Resolution, Pattern Correction, Exposure Area", Nikkei Microdevices, pp. 1-6, April 1995.		
	Okamoto, Y., et al., "A New Phase Shifting Mask Technology for Quarter Micron Photolithography", SPIE, Vol. 2512, pp. 311-318 (1995).		
	Pierrat, C., et al., "Required Optical Characteristics of Materials for Phase-Shifting Masks", Applied Optics, Vol. 34, No. 22, pp. 4923-4928, August 1, 1995.		
	Galan, G., et al., "Alternating Phase Shift Generation for Coplex Circuit Designs", SPIE, Vol. 2884, pp. 508-519, September 18-20, 1996.		
	Kanai, H., et al., "Sub-Quarter Micron Lithography with the Dual-Trench Type Alternating PSM", SPIE, Vol. 2793, pp. 165-173 (1996).		
	Ishiwata, N., et al., "Novel Alternating Phase Shift Mask with Improved Phase Accuracy", SPIE, Proceedings Of The 17th Annual Symposium On Photomask Technology And Management, Vol. 3236, pp. 243-249 (1997).		
	Morimoto, H., et al., "Next Generation Mask Strategy - Technologies are Ready for Mass Production of 256MDRAM?", SPIE, Vol. 3236, pp. 188-189 (1997).		
	Roman, B., et al., "Implications of Device Processing on Photomask CD Requirements", SPIE, Vol. 3236 (1997) (Abstract Only).		
	Nakae, A., et al., "A Proposal for Pattern Layout Rule in Application of Alternating Phase Shift Mask", SPIE, Vol. 3096, pp. 362-374 (1997).		
	Tsujimoto, E., et al., "Hierarchical Mask Data Design System (PROPHET) for Aerial Image Simulation, Automatic Phase-Shifter Placement, and Subpeak Overlap Checking", SPIE, Vol. 3096, pp. 163-172 (1997).		
	Yamamoto, K., et al., "Hierarchical Processing of Levenson-Type Phase Shifter Generation", Jpn. J. Appl. Phys., Vol. 36, Part 1, No. 12B, pp. 7499-7503, December 1997.		
	Gordon, R., et al., "Design and Analysis of Manufacturable Alternating Phase-Shifting Masks", Bacus News, Vol. 14, Issue 12, pp. 1-9, December 1998.		
	Nara, M., et al., "Phase Controllability Improvement for Alternating Phase Shift Mask", Dai Nippon Printing Co., Ltd. (16 pages).		
	Ohnuma, H., et al., "Lithography Computer Aided Design Technology for Embedded Memory in Logic", Jpn. J. Appl. Phys., Vol. 37, Part I, No. 12B, pp. 6686-6688, December 1998.		

EXAMINER:

Date Considered:

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 1.31.2002  
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

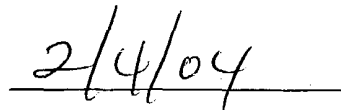
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<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
EXAMINER'S INITIALS	CITATION		
	Fukuda, H., "Node-Connection/Quantum Phase-Shifting Mask: Path to Below 0.3um Pitch, Proximity Effect Free, Random Interconnects and Memory Patterning", J. Vac. Sci. Technol. B, Vol. 17, No. 6, pp. 3291-3295, November/December 1999.		
	Spence, C., et al., "Integration of Optical Proximity Correction Strategies in Strong Phase Shifters Design for Poly-Gate Layers", Bacus News, Vol. 15, Issue 12, pp. 1, 4-13, December 1999.		
	Kuo, C., et al., "Extension of Deep-Ultraviolet Lithography for Patterning Logic Gates Using Alternating Phase Shifting Masks", J. Vac. Sci. Technol. B, Vol. 17, No. 6, pp. 3296-3300, November/December 1999.		
	Palmer, S., et al., "Dual Mask Model-Based Proximity Correction for High Performance 0.10um CMOS Process", The 44th International Conference on Electron, Ion and Photon Beam Technology and Nanofabrication Abstracts, pp. 18-19, May 30-June 2, 2000.		
	Pierrat, C., "Investigation of Proximity Effects in Alternating Aperture Phase Shifting Masks", Numerical Technologies, Inc. (11 pages).		
	Kikuchi, K., et al., "Method of Expanding Process Window for the Double Exposure Technique with alt-PSMs", Optical Microlithography XIII, Proceeding of SPIE, Vol. 4000, pp. 121-131 (2000).		
	Cote, M., et al., "A Practical Application of Full-Feature Alternating Phase-Shifting Technology for a Phase-Aware Standard-Cell Design Flow", Numerical Technologies Inc. (6 pages).		
	Heng, F., et al., "Application of Automated Design Migration to Alternating Phase Shift Mask Design", IBM Research Report RC 21978 (98769), February 26, 2001 (7 pages).		
	Wong, A., et al., "Alternating Phase-Shifting Mask with Reduced Aberration Sensitivity: Lithography Considerations", Proc. SPIE, Vol. 4346, pp. 1-9 (2001).		

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Date Considered:



EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.